

ABSTRACT

A slurry and related method for chemical mechanical polishing (CMP) of a metal film includes a solution containing at one halide ion and at least one halogen species which react with the metal film to form a surface layer on the film. The surface layer formed can be a metal halide layer. The surface layer can be removed by abrasive particles embedded in the polishing pad, or a thin inorganic layer coated on the polishing pad.